

UN0302P016-PD33

ROHS

P-Channel Enhancement Mode MOSFET

Product Summary

V _{DS}	-30V
I _D (T _C =25°C)	-20A
R _{DS(ON)} (@V _{GS} =-10V I _D =-10A)	≤23mΩ
R _{DS(ON)} (@V _{GS} =-4.5V I _D =-7.0A)	≤34mΩ

Features

- ◆ Surface Mount Package
- ◆ Lead Free Product is Acquired
- ◆ High Power and Current Handling Capability

Applications

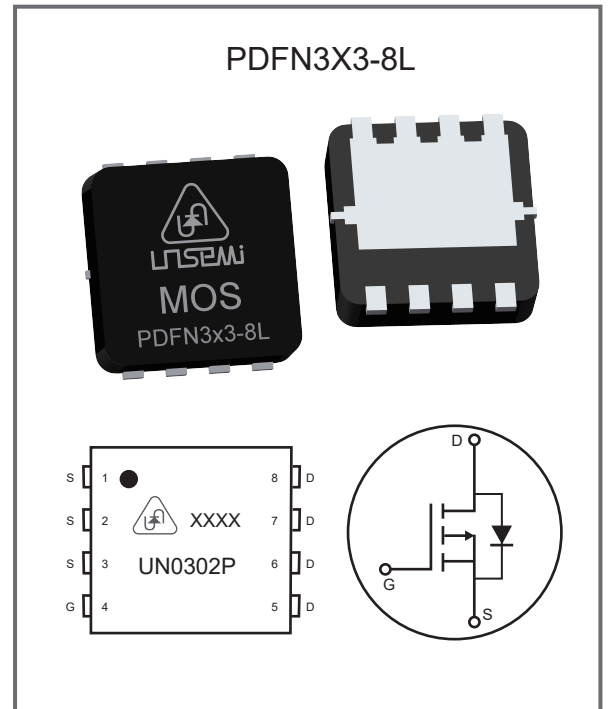
- ◆ Load Switch
- ◆ Battery Switch
- ◆ Power Management

Package Marking And Ordering information

Part Number	Package Type	Packaging	Reel(pcs)
UN0302P016-PD33	PDFN3X3-8L	Tape & Reel	5,000



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Absolute Maximum Ratings Tc = 25°C unless otherwise specified

Parameter	Symbol	Max.	Units
Drain to Source Voltage	V _{DS}	-30	V
Continuous Drain Current	I _D	-20	A
Pulsed Drain Current ¹⁾	I _{DM}	-60	A
Gate-Source Voltage	V _{GS}	±20	V
Power Dissipation	P _D	3.125	W
Junction and Storage Temperature Range	T _J , T _{stg}	-55~+150	°C

Thermal Characteristics

Parameter	Symbol	Typ.	Max.	Units
Thermal Resistance Junction-Ambient ²⁾	R _{θJA}	--	40	°C/W

Notes:

- 1) Repetitive Rating: Pulse width limited by maximum junction temperature.
- 2) Surface Mounted on FR4 Board, t≤10 sec.
- 3) Pulse Test: Pulse Width≤300μs, Duty Cycle≤2%.
- 4) Guaranteed by design, not subject to production.

Electrical Characteristics at Tc = 25°C unless otherwise specified

Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Units
STATIC PARAMETERS ³⁾						
Drain-Source Breakdown Voltage	BVDSS	VGS = 0V, ID = -250μA	-30	-33		V
Drain-Source Leakage Current	IDSS	VDS = -30V, VGS = 0V			-1.0	μA
Gate-Source Leakage Current	IGSS	VGS = ±20V, VDS = 0V			±100	nA
Gate-Source Threshold Voltage	VGS(TH)	VGS = VDS, ID = -250μA	-1.0	-1.5	-2.5	V
Drain-Source On-State Resistance	RDS(ON)	VGS = -10V, ID = -10A		16	23	mΩ
		VGS = -4.5V, ID = -7.0A		25	34	
Forward Transconductance	gfs	VDS = -15V, ID = -9.1A	10			S
BODY-DIODE PARAMETERS ³⁾						
Drain-Source Diode Forward Voltage	VSD	IS = -2.1A, VGS = 0V		-1.2		V
DYNAMIC PARAMETERS ⁴⁾						
Input Capacitance	Ciss	VGS = 0V VDS = -15V F = 1MHz		1600		pF
Output Capacitance	Coss			350		pF
Reverse Transfer Capacitance	Crss			300		pF
Gate Charge Total	Qg	VGS = -10V VDS = -15V ID = -9.1A		30		nC
Gate to Source Charge	Qgs			5.5		nC
Gate to Drain Charge	Qgd			8.0		nC
SWITCHING PARAMETERS ⁴⁾						
Turn-On Delay Time	td(ON)	VDS = -15V, VGS = -10V RGEN = 6.0Ω, ID = -1.0A		10		nS
Turn-On Rise Time	tr			15		nS
Turn-Off Delay Time	td(OFF)			110		nS
Turn-Off Fall Time	tf			70		nS



Electrical Characteristics Curves

Fig 1. Output Characteristics

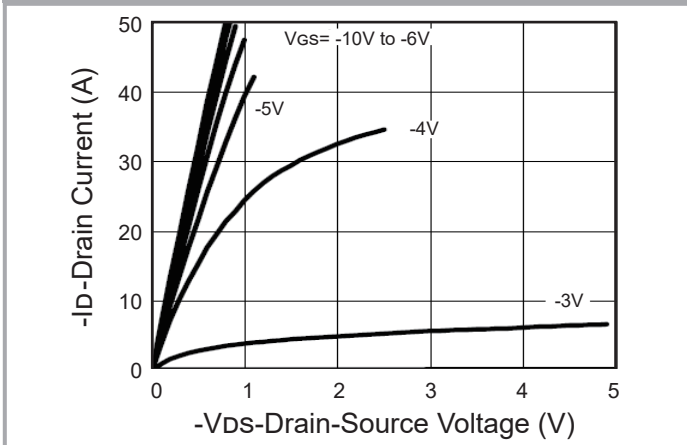


Fig 2. Typical Transfer Characteristic

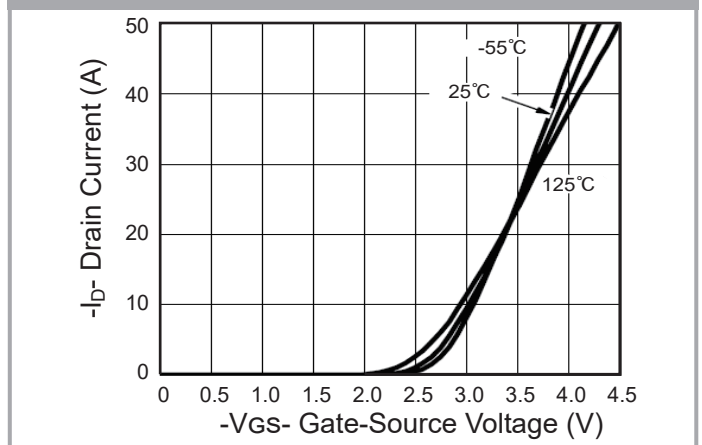


Fig 3. On-Resistance Vs Drain Current

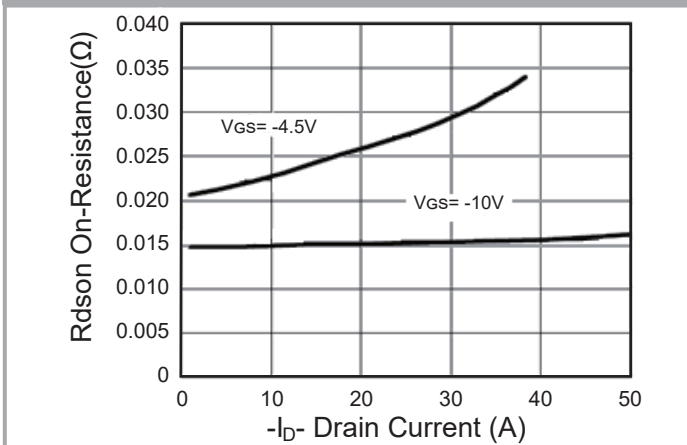


Fig 4. On-Resistance Vs Junction Temperature

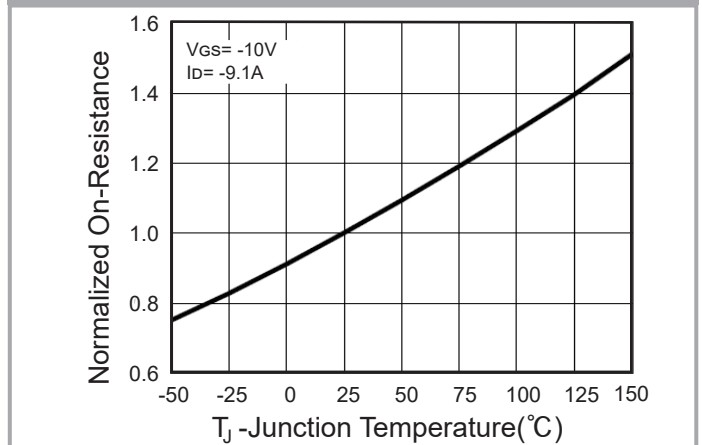


Fig 5. On-Resistance Vs Gate-Source Voltage

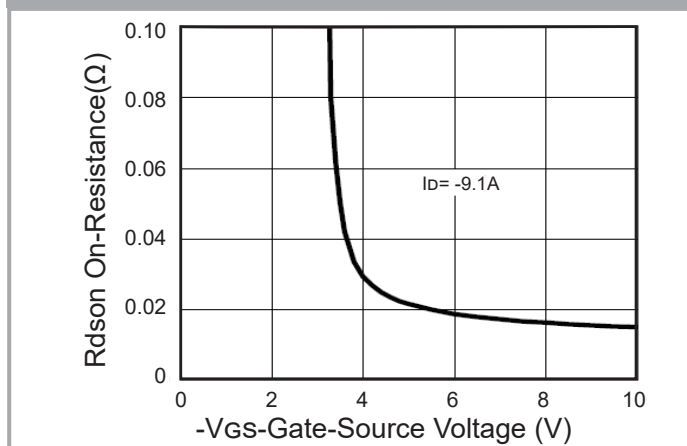
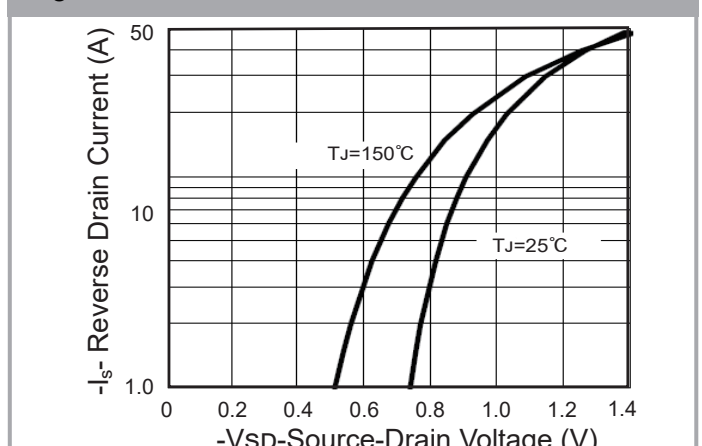


Fig 6. Source-Drain Diode Forward



Electrical Characteristics Curves

Fig 7. Capacitance Vs Drain-Source Voltage

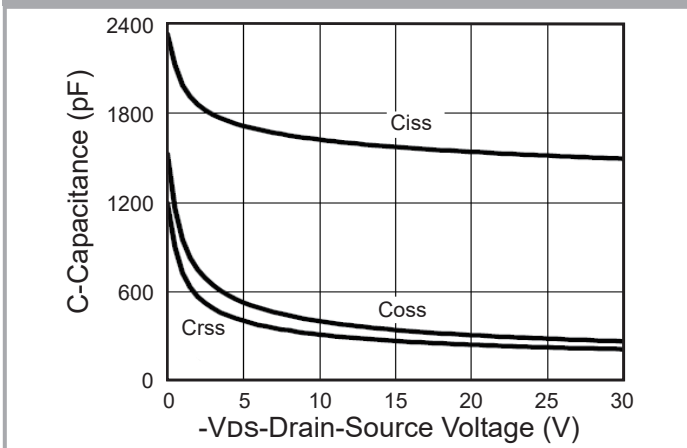


Fig 8. Safe Operation Area

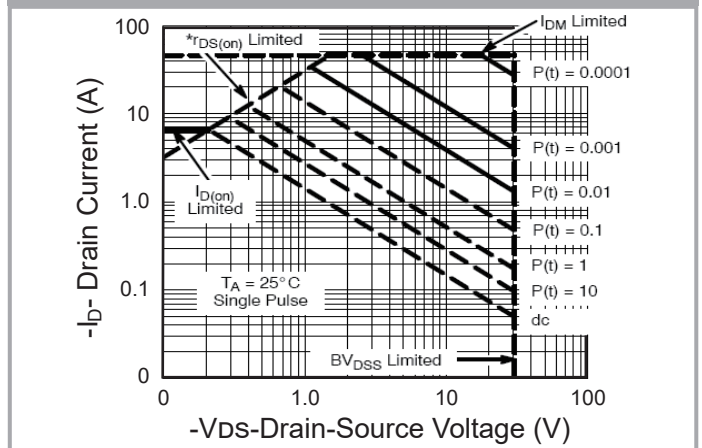


Fig 9. Power Derating

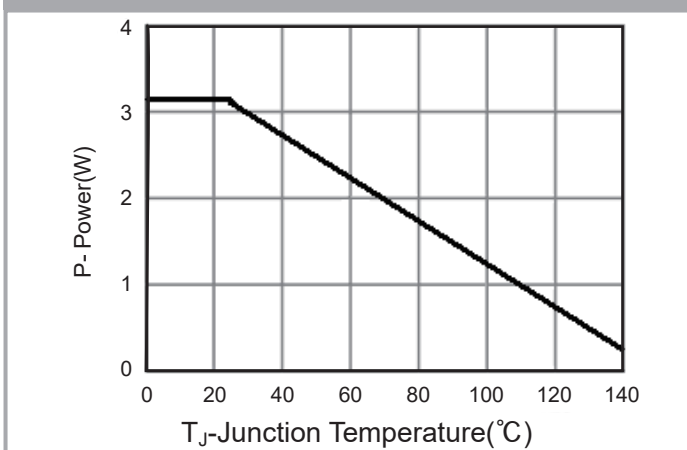


Fig 10. Drain Current Vs Junction Temperature

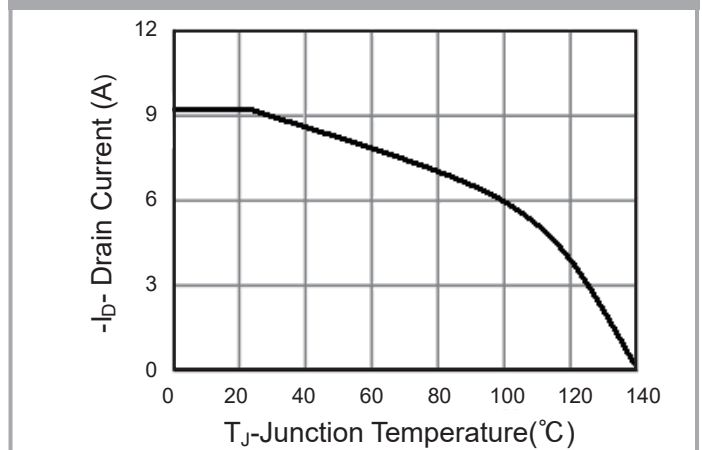
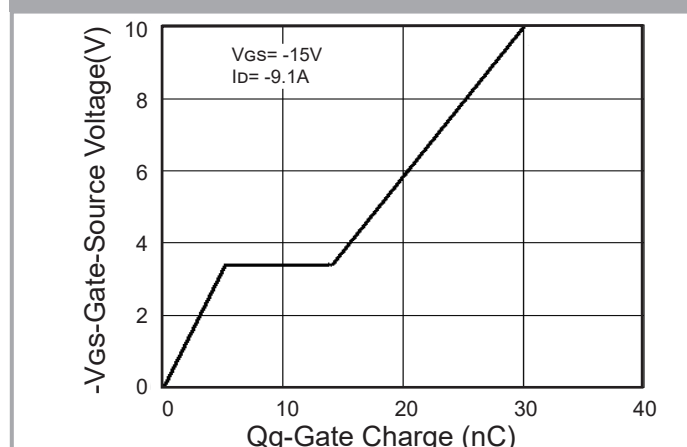
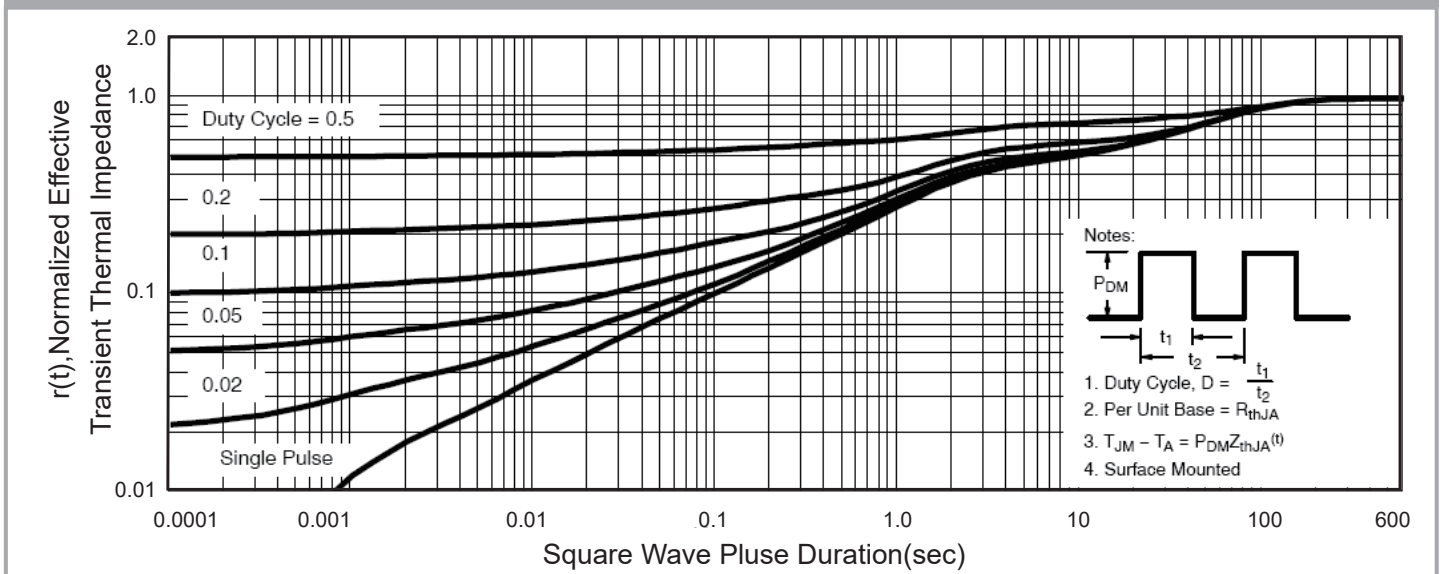


Fig 11. Gate Charge Characteristics



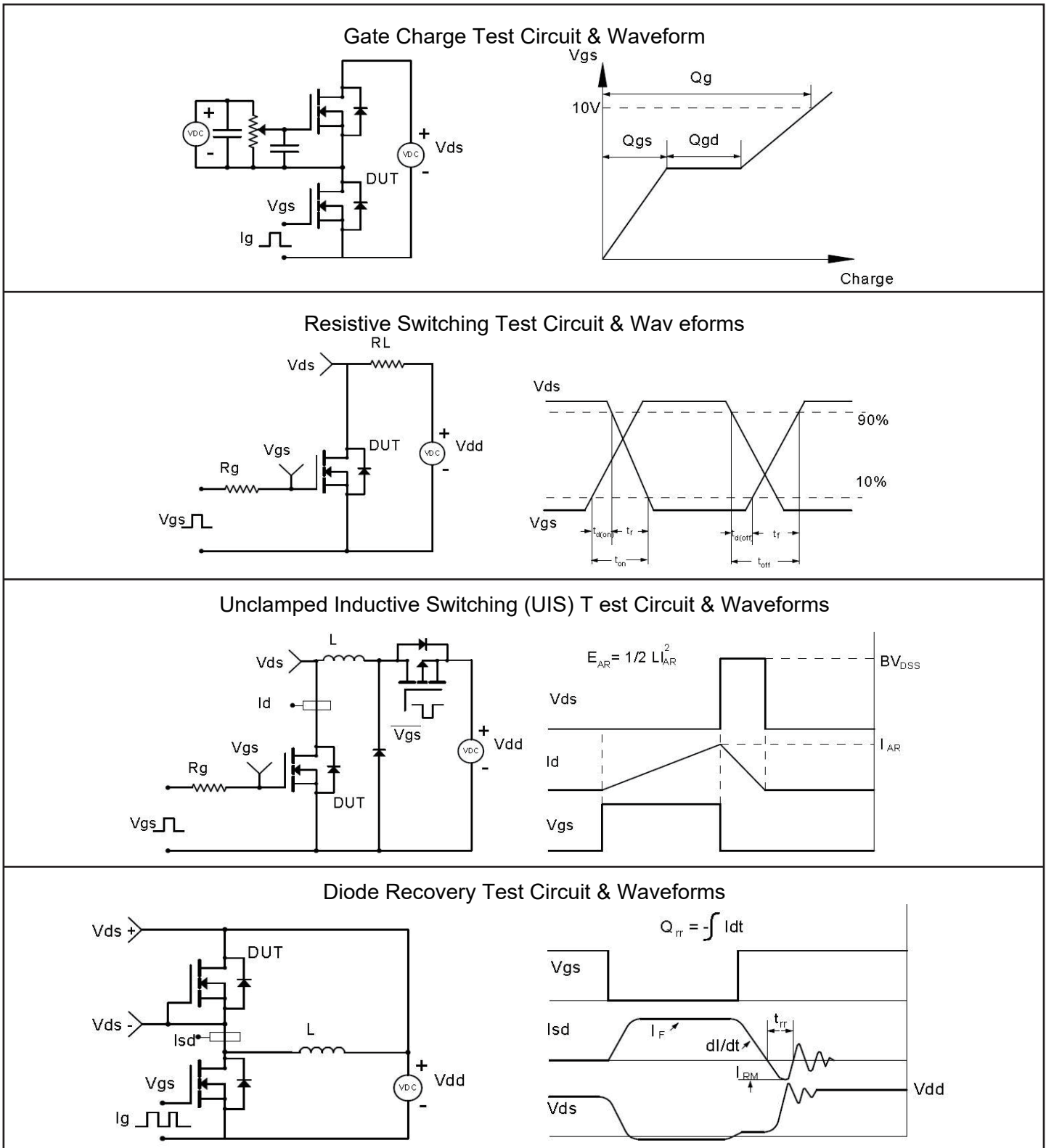
Electrical Characteristics Curves

Fig 12. Safe Normalized Maximum Transient Thermal Impedance



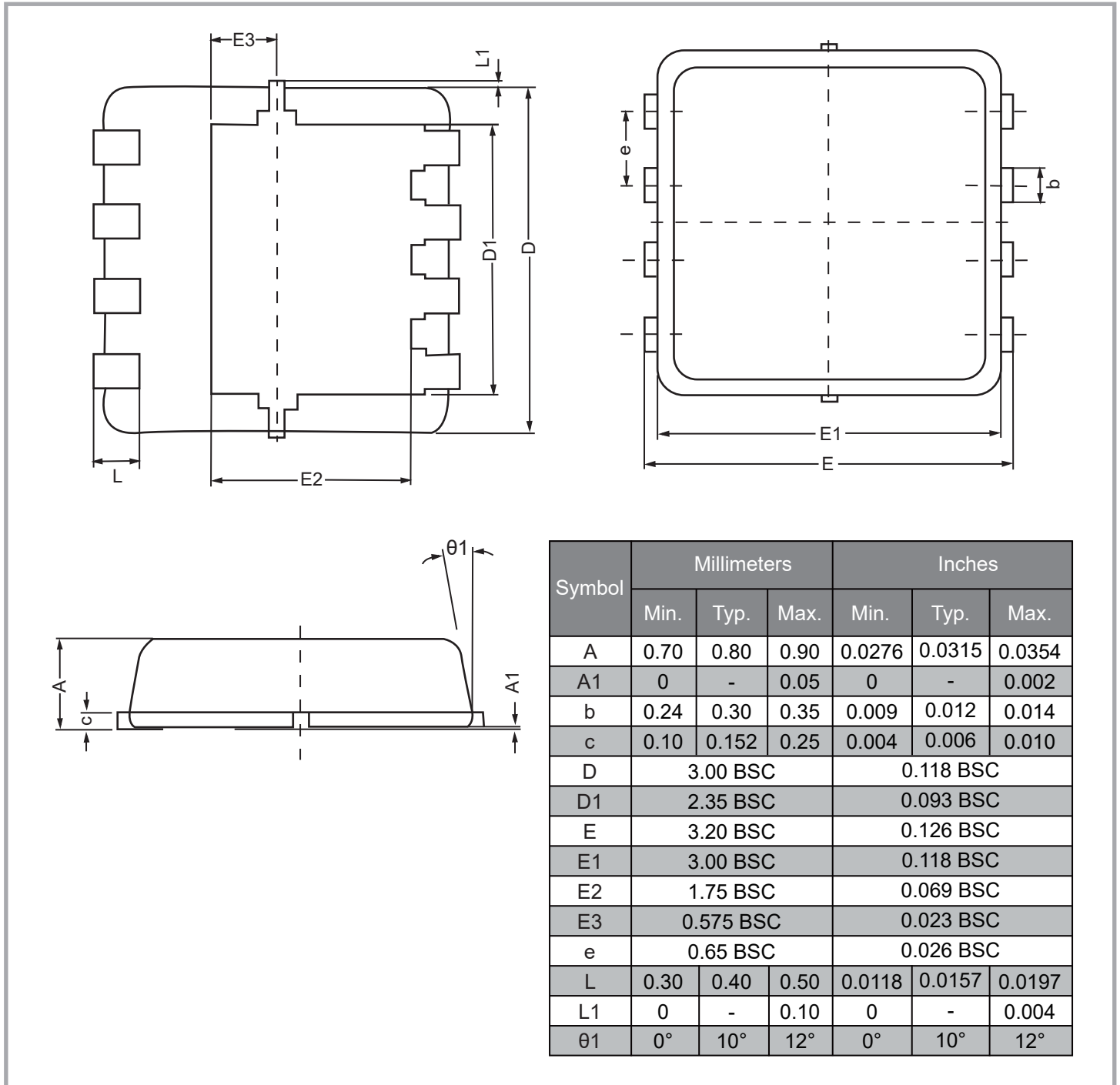


Test Circuit





PDFN3X3-8L Package Outline & Dimensions (Units: mm / in)



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